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(71) Applicant *(for all designated States except US)*: **SEMICONDUCTOR ENERGY LABORATORY CO., LTD.** [JP/JP]; 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **TSURUME, Takuya** [JP/JP]; c/o SEMICONDUCTOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP). **MARUYAMA, Junya** [JP/JP]; c/o SEMICONDUCTOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP). **DOZEN, Yoshitaka** [JP/JP]; c/o SEMICONDUCTOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

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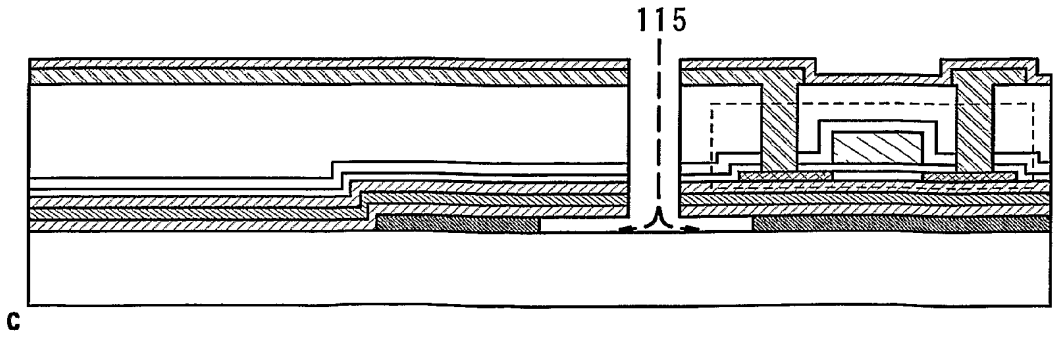
(54) Title: METHOD FOR MANUFACTURING INTEGRATED CIRCUIT




(57) Abstract: A method for separating an integrated circuit formed by a thin film having a novel structure or a method for transferring the integrated circuit to another substrate, that is, so-called transposing method, has not been proposed. According to the present invention, in the case that an integrated circuit having a thin film having a novel structure formed over a substrate via a release layer is separated, the release layer is removed in the state that the thin film integrated circuit is fixated, the thin film integrated circuit is transposed to a supporting substrate having an adhesion surface, and the thin film integrated circuit is transposed to another substrate having an adhesion surface with higher strength of adhesion than that of the supporting substrate.

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